

# AN79Lxx/AN79LxxM Series

3-pin negative output voltage regulator (100 mA type)

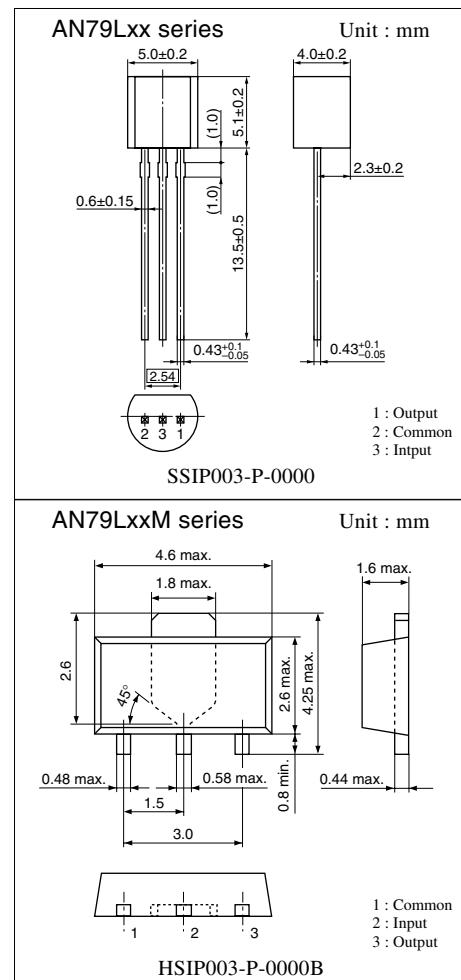
## ■ Overview

The AN79Lxx series and the AN79LxxM series are 3-pin, fixed negative output type monolithic voltage regulators.

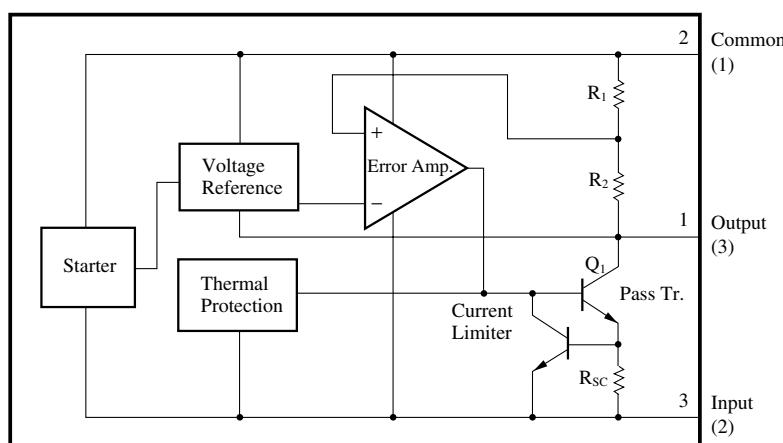
Stabilized fixed output voltage is obtained from unstable DC input voltage without using any external components. 12 types of output voltage are available: -4V, -5V, -6V, -7V, -8V, -9V, -10V, -12V, -15V, -18V, -20V and -24V. They can be used widely in power circuits with current capacity of up to 100mA.

## ■ Features

- No external components
- Output voltage: -4V, -5V, -6V, -7V, -8V, -9V, -10V, -12V, -15V, -18V, -20V, -24V
- Built-in overcurrent limit circuit
- Built-in thermal overload protection circuit



## ■ Block Diagram (AN79Lxx series)



Note) The number in ( ) shows the pin number for the AN79LxxM series.

### ■ Absolute Maximum Ratings at $T_a = 25^\circ\text{C}$

Parameter	Symbol	Rating	Unit
Input voltage	$V_I$	-35 *1	V
		-40 *2	V
Power dissipation	$P_D$	650 *3	mW
Operating ambient temperature	$T_{opr}$	-20 to +80	°C
Storage temperature	AN79Lxx series	-55 to +150	°C
	AN79LxxM series	-55 to +125	

\*1 AN79L04/M, AN79L05/M, AN79L06/M, AN79L07/M, AN79L08/M, AN79L09/M, AN79L10/M, AN79L12/M, AN79L15/M, AN79L18/M

\*2 AN79L20/M, AN79L24/M

\*3 Follow the derating curve. When  $T_j$  exceeds 150°C, the internal circuit cuts off the output.

AN79LxxM series is mounted on a standard board (glass epoxy: 20mm × 20mm × t1.7mm with Cu foil of 1cm<sup>2</sup> or more).

### ■ Electrical Characteristics at $T_a = 25^\circ\text{C}$

- AN79L04, AN79L04M (-4V type)

Parameter	Symbol	Conditions	Min	Typ	Max	Unit
Output voltage	$V_O$	$T_j = 25^\circ\text{C}$	-3.84	-4	-4.16	V
Output voltage tolerance	$V_O$	$V_I = -7 \text{ to } -19\text{V}, I_O = 1 \text{ to } 70\text{mA}$	-3.8	—	-4.2	V
Line regulation	$\text{REG}_{\text{IN}}$	$V_I = -6 \text{ to } -20\text{V}, T_j = 25^\circ\text{C}$	—	—	80	mV
		$V_I = -7 \text{ to } -17\text{V}, T_j = 25^\circ\text{C}$	—	—	40	mV
Load regulation	$\text{REG}_L$	$I_O = 1 \text{ to } 100\text{mA}, T_j = 25^\circ\text{C}$	—	10	60	mV
		$I_O = 1 \text{ to } 40\text{mA}, T_j = 25^\circ\text{C}$	—	4.5	30	mV
Bias current	$I_{\text{Bias}}$	$T_j = 25^\circ\text{C}$	—	3	5	mA
Bias current fluctuation to input	$\Delta I_{\text{Bias}(\text{IN})}$	$V_I = -7 \text{ to } -19\text{V}, T_j = 25^\circ\text{C}$	—	—	0.5	mA
Bias current fluctuation to load	$\Delta I_{\text{Bias}(L)}$	$I_O = 1 \text{ to } 40\text{mA}, T_j = 25^\circ\text{C}$	—	—	0.1	mA
Output noise voltage	$V_{\text{no}}$	$f = 10\text{Hz} \text{ to } 100\text{kHz}, T_a = 25^\circ\text{C}$	—	38	—	μV
Ripple rejection ratio	$\text{RR}$	$V_I = -7 \text{ to } -17\text{V}, f = 120\text{Hz}, T_a = 25^\circ\text{C}$	55	—	—	dB
Minimum input/output voltage difference	$V_{\text{DIF(min)}}$	$T_j = 25^\circ\text{C}$	—	0.8	—	V
Output short-circuit current	$I_O(\text{Short})$	$V_I = -35\text{V}, T_j = 25^\circ\text{C}$	—	200	—	mA
Output voltage temperature coefficient	$\Delta V_O/T_a$	$I_O = 5\text{mA}$	—	-0.4	—	mV/°C

Note 1) The specified condition  $T_j = 25^\circ\text{C}$  means that the test should be carried out within so short a test time (within 10ms) that the characteristic value drift due to the chip junction temperature rise can be ignored.

Note 2) Unless otherwise specified,  $V_I = -9\text{V}$ ,  $I_O = 40\text{mA}$ ,  $C_1 = 2\mu\text{F}$ ,  $C_O = 1\mu\text{F}$ ,  $T_j = 0 \text{ to } 125^\circ\text{C}$  (AN79L04) and  $T_j = 0 \text{ to } 100^\circ\text{C}$  (AN79L04M)

## ■ Electrical Characteristics at $T_a = 25^\circ\text{C}$ (continued)

- AN79L05, AN79L05M (-5V type)

Parameter	Symbol	Conditions	Min	Typ	Max	Unit
Output voltage	$V_o$	$T_j = 25^\circ\text{C}$	-4.8	-5	-5.2	V
Output voltage tolerance	$V_o$	$V_i = -8 \text{ to } -20\text{V}, I_o = 1 \text{ to } 70\text{mA}$	-4.75	—	-5.25	V
Line regulation	$\text{REG}_{\text{IN}}$	$V_i = -7 \text{ to } -21\text{V}, T_j = 25^\circ\text{C}$	—	—	100	mV
		$V_i = -8 \text{ to } -18\text{V}, T_j = 25^\circ\text{C}$	—	—	50	mV
Load regulation	$\text{REG}_L$	$I_o = 1 \text{ to } 100\text{mA}, T_j = 25^\circ\text{C}$	—	11	60	mV
		$I_o = 1 \text{ to } 40\text{mA}, T_j = 25^\circ\text{C}$	—	5	30	mV
Bias current	$I_{\text{Bias}}$	$T_j = 25^\circ\text{C}$	—	3	5	mA
Bias current fluctuation to input	$\Delta I_{\text{Bias}(\text{IN})}$	$V_i = -8 \text{ to } -20\text{V}, T_j = 25^\circ\text{C}$	—	—	0.5	mA
Bias current fluctuation to load	$\Delta I_{\text{Bias}(L)}$	$I_o = 1 \text{ to } 40\text{mA}, T_j = 25^\circ\text{C}$	—	—	0.1	mA
Output noise voltage	$V_{\text{no}}$	$f = 10\text{Hz} \text{ to } 100\text{kHz}, T_a = 25^\circ\text{C}$	—	40	—	$\mu\text{V}$
Ripple rejection ratio	RR	$V_i = -8 \text{ to } -18\text{V}, f = 120\text{Hz}, T_a = 25^\circ\text{C}$	55	—	—	dB
Minimum input/output voltage difference	$V_{\text{DIF(min)}}$	$T_j = 25^\circ\text{C}$	—	0.8	—	V
Output short-circuit current	$I_{\text{O(Short)}}$	$V_i = -35\text{V}, T_j = 25^\circ\text{C}$	—	200	—	mA
Output voltage temperature coefficient	$\Delta V_o/T_a$	$I_o = 5\text{mA}$	—	-0.4	—	$\text{mV}/^\circ\text{C}$

Note 1) The specified condition  $T_j = 25^\circ\text{C}$  means that the test should be carried out within so short a test time (within 10ms) that the characteristic value drift due to the chip junction temperature rise can be ignored.

Note 2) Unless otherwise specified,  $V_i = -10\text{V}$ ,  $I_o = 40\text{mA}$ ,  $C_i = 2\mu\text{F}$ ,  $C_o = 1\mu\text{F}$ ,  $T_j = 0 \text{ to } 125^\circ\text{C}$  (AN79L05) and  $T_j = 0 \text{ to } 100^\circ\text{C}$  (AN79L05M)

- AN79L06, AN79L06M (-6V type)

Parameter	Symbol	Conditions	Min	Typ	Max	Unit
Output voltage	$V_o$	$T_j = 25^\circ\text{C}$	-5.76	-6	-6.24	V
Output voltage tolerance	$V_o$	$V_i = -9 \text{ to } -21\text{V}, I_o = 1 \text{ to } 70\text{mA}$	-5.7	—	-6.3	V
Line regulation	$\text{REG}_{\text{IN}}$	$V_i = -8 \text{ to } -22\text{V}, T_j = 25^\circ\text{C}$	—	—	120	mV
		$V_i = -9 \text{ to } -19\text{V}, T_j = 25^\circ\text{C}$	—	—	60	mV
Load regulation	$\text{REG}_L$	$I_o = 1 \text{ to } 100\text{mA}, T_j = 25^\circ\text{C}$	—	12	60	mV
		$I_o = 1 \text{ to } 40\text{mA}, T_j = 25^\circ\text{C}$	—	5.5	30	mV
Bias current	$I_{\text{Bias}}$	$T_j = 25^\circ\text{C}$	—	3	5	mA
Bias current fluctuation to input	$\Delta I_{\text{Bias}(\text{IN})}$	$V_i = -9 \text{ to } -21\text{V}, T_j = 25^\circ\text{C}$	—	—	0.5	mA
Bias current fluctuation to load	$\Delta I_{\text{Bias}(L)}$	$I_o = 1 \text{ to } 40\text{mA}, T_j = 25^\circ\text{C}$	—	—	0.1	mA
Output noise voltage	$V_{\text{no}}$	$f = 10\text{Hz} \text{ to } 100\text{kHz}, T_a = 25^\circ\text{C}$	—	44	—	$\mu\text{V}$
Ripple rejection ratio	RR	$V_i = -9 \text{ to } -19\text{V}, f = 120\text{Hz}, T_a = 25^\circ\text{C}$	55	—	—	dB
Minimum input/output voltage difference	$V_{\text{DIF(min)}}$	$T_j = 25^\circ\text{C}$	—	0.8	—	V
Output short-circuit current	$I_{\text{O(Short)}}$	$V_i = -35\text{V}, T_j = 25^\circ\text{C}$	—	200	—	mA
Output voltage temperature coefficient	$\Delta V_o/T_a$	$I_o = 5\text{mA}$	—	-0.4	—	$\text{mV}/^\circ\text{C}$

Note 1) The specified condition  $T_j = 25^\circ\text{C}$  means that the test should be carried out within so short a test time (within 10ms) that the characteristic value drift due to the chip junction temperature rise can be ignored.

Note 2) Unless otherwise specified,  $V_i = -11\text{V}$ ,  $I_o = 40\text{mA}$ ,  $C_i = 2\mu\text{F}$ ,  $C_o = 1\mu\text{F}$ ,  $T_j = 0 \text{ to } 125^\circ\text{C}$  (AN79L06) and  $T_j = 0 \text{ to } 100^\circ\text{C}$  (AN79L06M)

### ■ Electrical Characteristics at $T_a = 25^\circ\text{C}$ (continued)

- AN79L07, AN79L07M (-7V type)

Parameter	Symbol	Conditions	Min	Typ	Max	Unit
Output voltage	$V_o$	$T_j = 25^\circ\text{C}$	-6.72	-7	-7.28	V
Output voltage tolerance	$V_o$	$V_i = -10 \text{ to } -22\text{V}, I_o = 1 \text{ to } 70\text{mA}$	-6.65	—	-7.35	V
Line regulation	$\text{REG}_{\text{IN}}$	$V_i = -9 \text{ to } -23\text{V}, T_j = 25^\circ\text{C}$	—	—	140	mV
		$V_i = -10 \text{ to } -20\text{V}, T_j = 25^\circ\text{C}$	—	—	70	mV
Load regulation	$\text{REG}_L$	$I_o = 1 \text{ to } 100\text{mA}, T_j = 25^\circ\text{C}$	—	13	70	mV
		$I_o = 1 \text{ to } 40\text{mA}, T_j = 25^\circ\text{C}$	—	6	40	mV
Bias current	$I_{\text{Bias}}$	$T_j = 25^\circ\text{C}$	—	3	5	mA
Bias current fluctuation to input	$\Delta I_{\text{Bias}(\text{IN})}$	$V_i = -10 \text{ to } -22\text{V}, T_j = 25^\circ\text{C}$	—	—	0.5	mA
Bias current fluctuation to load	$\Delta I_{\text{Bias}(L)}$	$I_o = 1 \text{ to } 40\text{mA}, T_j = 25^\circ\text{C}$	—	—	0.1	mA
Output noise voltage	$V_{\text{no}}$	$f = 10\text{Hz to } 100\text{kHz}, T_a = 25^\circ\text{C}$	—	48	—	$\mu\text{V}$
Ripple rejection ratio	RR	$V_i = -10 \text{ to } -20\text{V}, f = 120\text{Hz}, T_a = 25^\circ\text{C}$	54	—	—	dB
Minimum input/output voltage difference	$V_{\text{DIF(min)}}$	$T_j = 25^\circ\text{C}$	—	0.8	—	V
Output short-circuit current	$I_{\text{O(Short)}}$	$V_i = -35\text{V}, T_j = 25^\circ\text{C}$	—	200	—	mA
Output voltage temperature coefficient	$\Delta V_o/T_a$	$I_o = 5\text{mA}$	—	-0.5	—	$\text{mV}/^\circ\text{C}$

Note 1) The specified condition  $T_j = 25^\circ\text{C}$  means that the test should be carried out within so short a test time (within 10ms) that the characteristic value drift due to the chip junction temperature rise can be ignored.

Note 2) Unless otherwise specified,  $V_i = -12\text{V}$ ,  $I_o = 40\text{mA}$ ,  $C_i = 2\mu\text{F}$ ,  $C_o = 1\mu\text{F}$ ,  $T_j = 0 \text{ to } 125^\circ\text{C}$  (AN79L07) and  $T_j = 0 \text{ to } 100^\circ\text{C}$  (AN79L07M)

- AN79L08, AN79L08M (-8V type)

Parameter	Symbol	Conditions	Min	Typ	Max	Unit
Output voltage	$V_o$	$T_j = 25^\circ\text{C}$	-7.68	-8	-8.32	V
Output voltage tolerance	$V_o$	$V_i = -11 \text{ to } -23\text{V}, I_o = 1 \text{ to } 70\text{mA}$	-7.6	—	-8.4	V
Line regulation	$\text{REG}_{\text{IN}}$	$V_i = -10 \text{ to } -24\text{V}, T_j = 25^\circ\text{C}$	—	—	160	mV
		$V_i = -11 \text{ to } -21\text{V}, T_j = 25^\circ\text{C}$	—	—	80	mV
Load regulation	$\text{REG}_L$	$I_o = 1 \text{ to } 100\text{mA}, T_j = 25^\circ\text{C}$	—	15	80	mV
		$I_o = 1 \text{ to } 40\text{mA}, T_j = 25^\circ\text{C}$	—	7	40	mV
Bias current	$I_{\text{Bias}}$	$T_j = 25^\circ\text{C}$	—	3	5	mA
Bias current fluctuation to input	$\Delta I_{\text{Bias}(\text{IN})}$	$V_i = -11 \text{ to } -23\text{V}, T_j = 25^\circ\text{C}$	—	—	0.5	mA
Bias current fluctuation to load	$\Delta I_{\text{Bias}(L)}$	$I_o = 1 \text{ to } 40\text{mA}, T_j = 25^\circ\text{C}$	—	—	0.1	mA
Output noise voltage	$V_{\text{no}}$	$f = 10\text{Hz to } 100\text{kHz}, T_a = 25^\circ\text{C}$	—	52	—	$\mu\text{V}$
Ripple rejection ratio	RR	$V_i = -11 \text{ to } -21\text{V}, f = 120\text{Hz}, T_a = 25^\circ\text{C}$	54	—	—	dB
Minimum input/output voltage difference	$V_{\text{DIF(min)}}$	$T_j = 25^\circ\text{C}$	—	0.8	—	V
Output short-circuit current	$I_{\text{O(Short)}}$	$V_i = -35\text{V}, T_j = 25^\circ\text{C}$	—	200	—	mA
Output voltage temperature coefficient	$\Delta V_o/T_a$	$I_o = 5\text{mA}, T_j = 0 \text{ to } 125^\circ\text{C}$	—	-0.6	—	$\text{mV}/^\circ\text{C}$

Note 1) The specified condition  $T_j = 25^\circ\text{C}$  means that the test should be carried out within so short a test time (within 10ms) that the characteristic value drift due to the chip junction temperature rise can be ignored.

Note 2) Unless otherwise specified,  $V_i = -14\text{V}$ ,  $I_o = 40\text{mA}$ ,  $C_i = 2\mu\text{F}$ ,  $C_o = 1\mu\text{F}$ ,  $T_j = 0 \text{ to } 125^\circ\text{C}$  (AN79L08) and  $T_j = 0 \text{ to } 100^\circ\text{C}$  (AN79L08M)

■ Electrical Characteristics at  $T_a = 25^\circ\text{C}$  (continued)

- AN79L09, AN79L09M (-9V type)

Parameter	Symbol	Conditions	Min	Typ	Max	Unit
Output voltage	$V_o$	$T_j = 25^\circ\text{C}$	-8.64	-9	-9.36	V
Output voltage tolerance	$V_o$	$V_i = -12 \text{ to } -24\text{V}, I_o = 1 \text{ to } 70\text{mA}$	-8.55	—	-9.45	V
Line regulation	$\text{REG}_{\text{IN}}$	$V_i = -11 \text{ to } -25\text{V}, T_j = 25^\circ\text{C}$	—	—	160	mV
		$V_i = -12 \text{ to } -22\text{V}, T_j = 25^\circ\text{C}$	—	—	80	mV
Load regulation	$\text{REG}_L$	$I_o = 1 \text{ to } 100\text{mA}, T_j = 25^\circ\text{C}$	—	16	90	mV
		$I_o = 1 \text{ to } 40\text{mA}, T_j = 25^\circ\text{C}$	—	8	50	mV
Bias current	$I_{\text{Bias}}$	$T_j = 25^\circ\text{C}$	—	3	5	mA
Bias current fluctuation to input	$\Delta I_{\text{Bias}(\text{IN})}$	$V_i = -12 \text{ to } -24\text{V}, T_j = 25^\circ\text{C}$	—	—	0.5	mA
Bias current fluctuation to load	$\Delta I_{\text{Bias}(L)}$	$I_o = 1 \text{ to } 40\text{mA}, T_j = 25^\circ\text{C}$	—	—	0.1	mA
Output noise voltage	$V_{\text{no}}$	$f = 10\text{Hz} \text{ to } 100\text{kHz}, T_a = 25^\circ\text{C}$	—	58	—	$\mu\text{V}$
Ripple rejection ratio	RR	$V_i = -12 \text{ to } -22\text{V}, f = 120\text{Hz}, T_a = 25^\circ\text{C}$	53	—	—	dB
Minimum input/output voltage difference	$V_{\text{DIF(min)}}$	$T_j = 25^\circ\text{C}$	—	0.8	—	V
Output short-circuit current	$I_{\text{O(Short)}}$	$V_i = -35\text{V}, T_j = 25^\circ\text{C}$	—	200	—	mA
Output voltage temperature coefficient	$\Delta V_o/T_a$	$I_o = 5\text{mA}, T_j = 0 \text{ to } 125^\circ\text{C}$	—	-0.6	—	$\text{mV}/^\circ\text{C}$

Note 1) The specified condition  $T_j = 25^\circ\text{C}$  means that the test should be carried out within so short a test time (within 10ms) that the characteristic value drift due to the chip junction temperature rise can be ignored.

Note 2) Unless otherwise specified,  $V_i = -15\text{V}$ ,  $I_o = 40\text{mA}$ ,  $C_i = 2\mu\text{F}$ ,  $C_o = 1\mu\text{F}$ ,  $T_j = 0 \text{ to } 125^\circ\text{C}$  (AN79L09) and  $T_j = 0 \text{ to } 100^\circ\text{C}$  (AN79L09M)

- AN79L10, AN79L10M (-10V type)

Parameter	Symbol	Conditions	Min	Typ	Max	Unit
Output voltage	$V_o$	$T_j = 25^\circ\text{C}$	-9.6	-10	-10.4	V
Output voltage tolerance	$V_o$	$V_i = -13 \text{ to } -25\text{V}, I_o = 1 \text{ to } 70\text{mA}$	-9.5	—	-10.5	V
Line regulation	$\text{REG}_{\text{IN}}$	$V_i = -12 \text{ to } -26\text{V}, T_j = 25^\circ\text{C}$	—	—	160	mV
		$V_i = -13 \text{ to } -23\text{V}, T_j = 25^\circ\text{C}$	—	—	80	mV
Load regulation	$\text{REG}_L$	$I_o = 1 \text{ to } 100\text{mA}, T_j = 25^\circ\text{C}$	—	17	100	mV
		$I_o = 1 \text{ to } 40\text{mA}, T_j = 25^\circ\text{C}$	—	9	50	mV
Bias current	$I_{\text{Bias}}$	$T_j = 25^\circ\text{C}$	—	3	5	mA
Bias current fluctuation to input	$\Delta I_{\text{Bias}(\text{IN})}$	$V_i = -13 \text{ to } -25\text{V}, T_j = 25^\circ\text{C}$	—	—	0.5	mA
Bias current fluctuation to load	$\Delta I_{\text{Bias}(L)}$	$I_o = 1 \text{ to } 40\text{mA}, T_j = 25^\circ\text{C}$	—	—	0.1	mA
Output noise voltage	$V_{\text{no}}$	$f = 10\text{Hz} \text{ to } 100\text{kHz}, T_a = 25^\circ\text{C}$	—	65	—	$\mu\text{V}$
Ripple rejection ratio	RR	$V_i = -13 \text{ to } -23\text{V}, f = 120\text{Hz}, T_a = 25^\circ\text{C}$	53	—	—	dB
Minimum input/output voltage difference	$V_{\text{DIF(min)}}$	$T_j = 25^\circ\text{C}$	—	0.8	—	V
Output short-circuit current	$I_{\text{O(Short)}}$	$V_i = -35\text{V}, T_j = 25^\circ\text{C}$	—	200	—	mA
Output voltage temperature coefficient	$\Delta V_o/T_a$	$I_o = 5\text{mA}$	—	-0.7	—	$\text{mV}/^\circ\text{C}$

Note 1) The specified condition  $T_j = 25^\circ\text{C}$  means that the test should be carried out within so short a test time (within 10ms) that the characteristic value drift due to the chip junction temperature rise can be ignored.

Note 2) Unless otherwise specified,  $V_i = -16\text{V}$ ,  $I_o = 40\text{mA}$ ,  $C_i = 2\mu\text{F}$ ,  $C_o = 1\mu\text{F}$ ,  $T_j = 0 \text{ to } 125^\circ\text{C}$  (AN79L10) and  $T_j = 0 \text{ to } 100^\circ\text{C}$  (AN79L10M)

■ Electrical Characteristics at  $T_a = 25^\circ\text{C}$  (continued)

- AN79L12, AN79L12M (-12V type)

Parameter	Symbol	Conditions	Min	Typ	Max	Unit
Output voltage	$V_o$	$T_j = 25^\circ\text{C}$	-11.5	-12	-12.5	V
Output voltage tolerance	$V_o$	$V_i = -15 \text{ to } -27\text{V}, I_o = 1 \text{ to } 70\text{mA}$	-11.4	—	-12.6	V
Line regulation	$\text{REG}_{\text{IN}}$	$V_i = -14.5 \text{ to } -30\text{V}, T_j = 25^\circ\text{C}$	—	—	200	mV
		$V_i = -15 \text{ to } -25\text{V}, T_j = 25^\circ\text{C}$	—	—	100	mV
Load regulation	$\text{REG}_L$	$I_o = 1 \text{ to } 100\text{mA}, T_j = 25^\circ\text{C}$	—	20	100	mV
		$I_o = 1 \text{ to } 40\text{mA}, T_j = 25^\circ\text{C}$	—	10	50	mV
Bias current	$I_{\text{Bias}}$	$T_j = 25^\circ\text{C}$	—	3	5	mA
Bias current fluctuation to input	$\Delta I_{\text{Bias}(\text{IN})}$	$V_i = -15 \text{ to } -27\text{V}, T_j = 25^\circ\text{C}$	—	—	0.5	mA
Bias current fluctuation to load	$\Delta I_{\text{Bias}(L)}$	$I_o = 1 \text{ to } 40\text{mA}, T_j = 25^\circ\text{C}$	—	—	0.1	mA
Output noise voltage	$V_{\text{no}}$	$f = 10\text{Hz} \text{ to } 100\text{kHz}, T_a = 25^\circ\text{C}$	—	75	—	$\mu\text{V}$
Ripple rejection ratio	RR	$V_i = -15 \text{ to } -25\text{V}, f = 120\text{Hz}, T_a = 25^\circ\text{C}$	52	—	—	dB
Minimum input/output voltage difference	$V_{\text{DIF(min)}}$	$T_j = 25^\circ\text{C}$	—	0.8	—	V
Output short-circuit current	$I_{\text{O(Short)}}$	$V_i = -35\text{V}, T_j = 25^\circ\text{C}$	—	200	—	mA
Output voltage temperature coefficient	$\Delta V_o/T_a$	$I_o = 5\text{mA}$	—	-0.8	—	$\text{mV}/^\circ\text{C}$

Note 1) The specified condition  $T_j = 25^\circ\text{C}$  means that the test should be carried out within so short a test time (within 10ms) that the characteristic value drift due to the chip junction temperature rise can be ignored.

Note 2) Unless otherwise specified,  $V_i = -19\text{V}$ ,  $I_o = 40\text{mA}$ ,  $C_i = 2\mu\text{F}$ ,  $C_o = 1\mu\text{F}$ ,  $T_j = 0 \text{ to } 125^\circ\text{C}$  (AN79L12) and  $T_j = 0 \text{ to } 100^\circ\text{C}$  (AN79L12M)

- AN79L15, AN79L15M (-15V type)

Parameter	Symbol	Conditions	Min	Typ	Max	Unit
Output voltage	$V_o$	$T_j = 25^\circ\text{C}$	-14.4	-15	-15.6	V
Output voltage tolerance	$V_o$	$V_i = -18 \text{ to } -28\text{V}, I_o = 1 \text{ to } 70\text{mA}$	-14.25	—	-15.75	V
Line regulation	$\text{REG}_{\text{IN}}$	$V_i = -17.5 \text{ to } -33\text{V}, T_j = 25^\circ\text{C}$	—	—	200	mV
		$V_i = -18 \text{ to } -28\text{V}, T_j = 25^\circ\text{C}$	—	—	100	mV
Load regulation	$\text{REG}_L$	$I_o = 1 \text{ to } 100\text{mA}, T_j = 25^\circ\text{C}$	—	25	130	mV
		$I_o = 1 \text{ to } 40\text{mA}, T_j = 25^\circ\text{C}$	—	12	60	mV
Bias current	$I_{\text{Bias}}$	$T_j = 25^\circ\text{C}$	—	3	5	mA
Bias current fluctuation to input	$\Delta I_{\text{Bias}(\text{IN})}$	$V_i = -18 \text{ to } -30\text{V}, T_j = 25^\circ\text{C}$	—	—	0.5	mA
Bias current fluctuation to load	$\Delta I_{\text{Bias}(L)}$	$I_o = 1 \text{ to } 40\text{mA}, T_j = 25^\circ\text{C}$	—	—	0.1	mA
Output noise voltage	$V_{\text{no}}$	$f = 10\text{Hz} \text{ to } 100\text{kHz}, T_a = 25^\circ\text{C}$	—	90	—	$\mu\text{V}$
Ripple rejection ratio	RR	$V_i = -18 \text{ to } -28\text{V}, f = 120\text{Hz}, T_a = 25^\circ\text{C}$	51	—	—	dB
Minimum input/output voltage difference	$V_{\text{DIF(min)}}$	$T_j = 25^\circ\text{C}$	—	0.8	—	V
Output short-circuit current	$I_{\text{O(Short)}}$	$V_i = -35\text{V}, T_j = 25^\circ\text{C}$	—	200	—	mA
Output voltage temperature coefficient	$\Delta V_o/T_a$	$I_o = 5\text{mA}$	—	-0.9	—	$\text{mV}/^\circ\text{C}$

Note 1) The specified condition  $T_j = 25^\circ\text{C}$  means that the test should be carried out within so short a test time (within 10ms) that the characteristic value drift due to the chip junction temperature rise can be ignored.

Note 2) Unless otherwise specified,  $V_i = -23\text{V}$ ,  $I_o = 40\text{mA}$ ,  $C_i = 2\mu\text{F}$ ,  $C_o = 1\mu\text{F}$ ,  $T_j = 0 \text{ to } 125^\circ\text{C}$  (AN79L15) and  $T_j = 0 \text{ to } 100^\circ\text{C}$  (AN79L15M)

■ Electrical Characteristics at  $T_a = 25^\circ\text{C}$  (continued)

- AN79L18, AN79L18M (-18V type)

Parameter	Symbol	Conditions	Min	Typ	Max	Unit
Output voltage	$V_o$	$T_j = 25^\circ\text{C}$	-17.3	-18	-18.7	V
Output voltage tolerance	$V_o$	$V_i = -21 \text{ to } -33\text{V}, I_o = 1 \text{ to } 70\text{mA}$	-17.1	—	-18.9	V
Line regulation	$\text{REG}_{\text{IN}}$	$V_i = -21 \text{ to } -33\text{V}, T_j = 25^\circ\text{C}$	—	—	200	mV
		$V_i = -21 \text{ to } -32\text{V}, T_j = 25^\circ\text{C}$	—	—	100	mV
Load regulation	$\text{REG}_L$	$I_o = 1 \text{ to } 100\text{mA}, T_j = 25^\circ\text{C}$	—	30	160	mV
		$I_o = 1 \text{ to } 40\text{mA}, T_j = 25^\circ\text{C}$	—	15	80	mV
Bias current	$I_{\text{Bias}}$	$T_j = 25^\circ\text{C}$	—	3	5	mA
Bias current fluctuation to input	$\Delta I_{\text{Bias}(\text{IN})}$	$V_i = -21 \text{ to } -33\text{V}, T_j = 25^\circ\text{C}$	—	—	0.5	mA
Bias current fluctuation to load	$\Delta I_{\text{Bias}(L)}$	$I_o = 1 \text{ to } 40\text{mA}, T_j = 25^\circ\text{C}$	—	—	0.1	mA
Output noise voltage	$V_{\text{no}}$	$f = 10\text{Hz} \text{ to } 100\text{kHz}, T_a = 25^\circ\text{C}$	—	110	—	$\mu\text{V}$
Ripple rejection ratio	RR	$V_i = -22 \text{ to } -32\text{V}, f = 120\text{Hz}, T_a = 25^\circ\text{C}$	50	—	—	dB
Minimum input/output voltage difference	$V_{\text{DIF(min)}}$	$T_j = 25^\circ\text{C}$	—	0.8	—	V
Output short-circuit current	$I_{\text{O(Short)}}$	$V_i = -35\text{V}, T_j = 25^\circ\text{C}$	—	200	—	mA
Output voltage temperature coefficient	$\Delta V_o/T_a$	$I_o = 5\text{mA}$	—	-1	—	$\text{mV}/^\circ\text{C}$

Note 1) The specified condition  $T_j = 25^\circ\text{C}$  means that the test should be carried out within so short a test time (within 10ms) that the characteristic value drift due to the chip junction temperature rise can be ignored.

Note 2) Unless otherwise specified,  $V_i = -27\text{V}$ ,  $I_o = 40\text{mA}$ ,  $C_l = 2\mu\text{F}$ ,  $C_o = 1\mu\text{F}$ ,  $T_j = 0 \text{ to } 125^\circ\text{C}$  (AN79L18) and  $T_j = 0 \text{ to } 100^\circ\text{C}$  (AN79L18M)

- AN79L20, AN79L20M (-20V type)

Parameter	Symbol	Conditions	Min	Typ	Max	Unit
Output voltage	$V_o$	$T_j = 25^\circ\text{C}$	-19.2	-20	-20.8	V
Output voltage tolerance	$V_o$	$V_i = -23 \text{ to } -35\text{V}, I_o = 1 \text{ to } 70\text{mA}$	-19	—	-21	V
Line regulation	$\text{REG}_{\text{IN}}$	$V_i = -23 \text{ to } -35\text{V}, T_j = 25^\circ\text{C}$	—	—	200	mV
		$V_i = -24 \text{ to } -34\text{V}, T_j = 25^\circ\text{C}$	—	—	100	mV
Load regulation	$\text{REG}_L$	$I_o = 1 \text{ to } 100\text{mA}, T_j = 25^\circ\text{C}$	—	35	180	mV
		$I_o = 1 \text{ to } 40\text{mA}, T_j = 25^\circ\text{C}$	—	17	90	mV
Bias current	$I_{\text{Bias}}$	$T_j = 25^\circ\text{C}$	—	3	5	mA
Bias current fluctuation to input	$\Delta I_{\text{Bias}(\text{IN})}$	$V_i = -23 \text{ to } -35\text{V}, T_j = 25^\circ\text{C}$	—	—	0.5	mA
Bias current fluctuation to load	$\Delta I_{\text{Bias}(L)}$	$I_o = 1 \text{ to } 40\text{mA}, T_j = 25^\circ\text{C}$	—	—	0.1	mA
Output noise voltage	$V_{\text{no}}$	$f = 10\text{Hz} \text{ to } 100\text{kHz}, T_a = 25^\circ\text{C}$	—	135	—	$\mu\text{V}$
Ripple rejection ratio	RR	$V_i = -24 \text{ to } -34\text{V}, f = 120\text{Hz}, T_a = 25^\circ\text{C}$	49	—	—	dB
Minimum input/output voltage difference	$V_{\text{DIF(min)}}$	$T_j = 25^\circ\text{C}$	—	0.8	—	V
Output short-circuit current	$I_{\text{O(Short)}}$	$V_i = -35\text{V}, T_j = 25^\circ\text{C}$	—	200	—	mA
Output voltage temperature coefficient	$\Delta V_o/T_a$	$I_o = 5\text{mA}$	—	-1	—	$\text{mV}/^\circ\text{C}$

Note 1) The specified condition  $T_j = 25^\circ\text{C}$  means that the test should be carried out within so short a test time (within 10ms) that the characteristic value drift due to the chip junction temperature rise can be ignored.

Note 2) Unless otherwise specified,  $V_i = -29\text{V}$ ,  $I_o = 40\text{mA}$ ,  $C_l = 2\mu\text{F}$ ,  $C_o = 1\mu\text{F}$ ,  $T_j = 0 \text{ to } 125^\circ\text{C}$  (AN79L20) and  $T_j = 0 \text{ to } 100^\circ\text{C}$  (AN79L20M)

## ■ Electrical Characteristics at $T_a = 25^\circ\text{C}$ (continued)

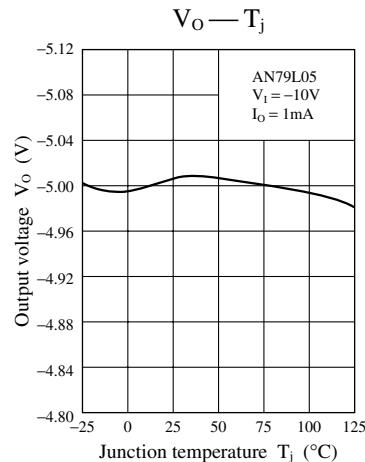
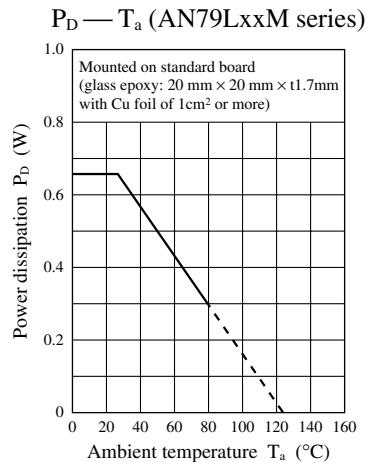
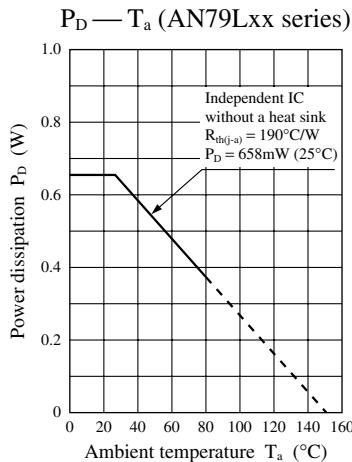
- AN79L24, AN79L24M (-24V type)

Parameter	Symbol	Conditions	Min	Typ	Max	Unit
Output voltage	$V_o$	$T_j = 25^\circ\text{C}$	-23	-24	-25	V
Output voltage tolerance	$V_o$	$V_i = -27 \text{ to } -38\text{V}, I_o = 1 \text{ to } 70\text{mA}$	-22.8	—	-25.2	V
Line regulation	$\text{REG}_{\text{IN}}$	$V_i = -27 \text{ to } -38\text{V}, T_j = 25^\circ\text{C}$	—	—	200	mV
		$V_i = -27 \text{ to } -37\text{V}, T_j = 25^\circ\text{C}$	—	—	100	mV
Load regulation	$\text{REG}_L$	$I_o = 1 \text{ to } 100\text{mA}, T_j = 25^\circ\text{C}$	—	40	200	mV
		$I_o = 1 \text{ to } 40\text{mA}, T_j = 25^\circ\text{C}$	—	20	100	mV
Bias current	$I_{\text{Bias}}$	$T_j = 25^\circ\text{C}$	—	3	5	mA
Bias current fluctuation to input	$\Delta I_{\text{Bias}(\text{IN})}$	$V_i = -27 \text{ to } -38\text{V}, T_j = 25^\circ\text{C}$	—	—	0.5	mA
Bias current fluctuation to load	$\Delta I_{\text{Bias}(L)}$	$I_o = 1 \text{ to } 40\text{mA}, T_j = 25^\circ\text{C}$	—	—	0.1	mA
Output noise voltage	$V_{\text{no}}$	$f = 10\text{Hz} \text{ to } 100\text{kHz}, T_a = 25^\circ\text{C}$	—	170	—	$\mu\text{V}$
Ripple rejection ratio	RR	$V_i = -28 \text{ to } -38\text{V}, f = 120\text{Hz}, T_a = 25^\circ\text{C}$	49	—	—	dB
Minimum input/output voltage difference	$V_{\text{DIF(min)}}$	$T_j = 25^\circ\text{C}$	—	0.8	—	V
Output short-circuit current	$I_o(\text{Short})$	$V_i = -35\text{V}, T_j = 25^\circ\text{C}$	—	200	—	mA
Output voltage temperature coefficient	$\Delta V_o/T_a$	$I_o = 5\text{mA}$	—	-1	—	$\text{mV}/^\circ\text{C}$

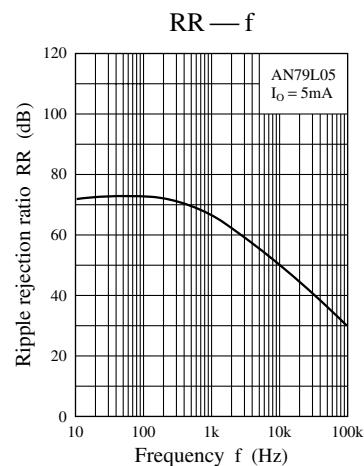
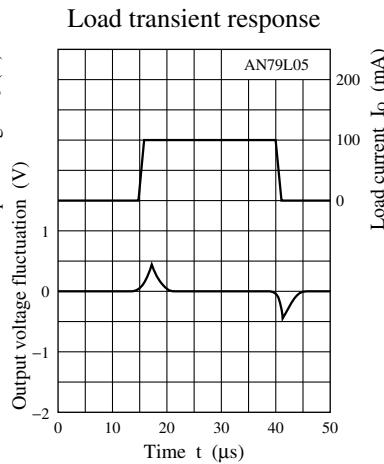
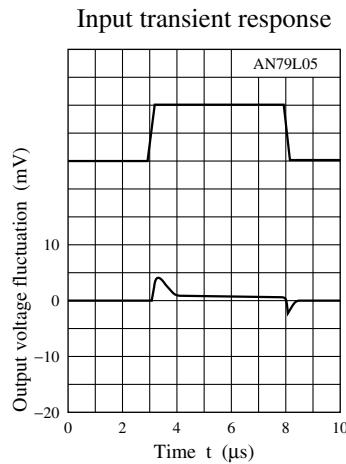
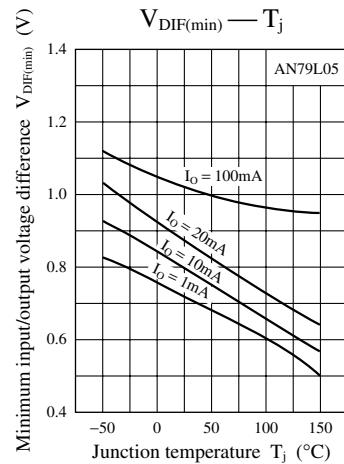
Note 1) The specified condition  $T_j = 25^\circ\text{C}$  means that the test should be carried out within so short a test time (within 10ms) that the characteristic value drift due to the chip junction temperature rise can be ignored.

Note 2) Unless otherwise specified,  $V_i = -33\text{V}$ ,  $I_o = 40\text{mA}$ ,  $C_i = 2\mu\text{F}$ ,  $C_o = 1\mu\text{F}$ ,  $T_j = 0 \text{ to } 125^\circ\text{C}$  (AN79L24) and  $T_j = 0 \text{ to } 100^\circ\text{C}$  (AN79L24M)

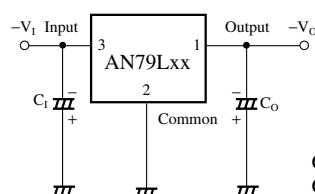
## ■ Main Characteristics



## ■ Main Characteristics (continued)



## ■ Basic Regulator Circuit



Connect  $C_1$  of  $2\mu F$  when the input line is long.  
 $C_o$  improves the transient response.  $1\mu F$

## ■ Usage Notes

### 1. Cautions for a basic circuit

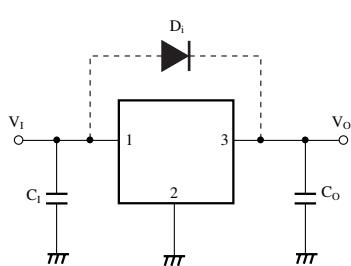


Figure 1

**C<sub>i</sub>:** When a wiring from a smoothing circuit to a three-pin regulator is long, it is likely to oscillate at output. A capacitor of 0.1μF to 0.47μF should be connected near an input pin.

**C<sub>o</sub>:** Deadly needed to prevent from oscillation (0.33μF to 1.0μF). It is recommended to use a capacitor of a small internal impedance (ex. tantalum capacitor) when using it under a low temperature.

When any sudden change of load current is likely to occur, connect an electrolytic capacitor of 10μF to 100μF to improve a transitional response of output voltage.

**D<sub>i</sub>:** Normally unnecessary. But add it in the case that there is a residual voltage at the output capacitor Co even after switching off the supply power because a current is likely to flow into an output pin of the IC and damage the IC.

### 2. Other caution items

#### 1) Short-circuit between the input pin and GND pin

If the input pin is short-circuited to GND or is cut off when a large capacitance capacitor has been connected to the IC's load, a voltage of a capacitor connected to an output pin is applied between input/output of the IC and this likely results in damage of the IC. It is necessary, therefore, to connect a diode, as shown in figure 2, to counter the reverse bias between input/output pins.

#### 2) Floating of GND pin

If a GND pin is made floating in an operating mode, an unstabilized input voltage is outputted. In this case, a thermal protection circuit inside the IC does not normally operate. In this state, if the load is short-circuited or overloaded, it is likely to damage the IC.

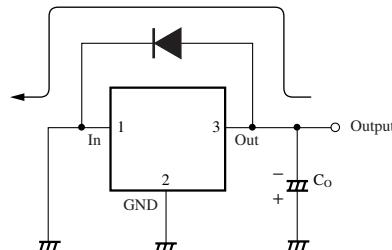
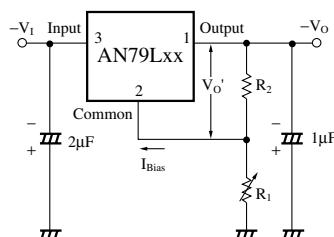


Figure 2

## ■ Application Circuit Example



$$|V_{O'}| = V_{O'} \left( 1 + \frac{R_1}{R_2} \right) + I_Q R_1$$

Note)  $V_{O'}$  varies due to sample to sample variation of  $I_{Bias}$ .  
Never fail to adjust individually with  $R_1$ .

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